

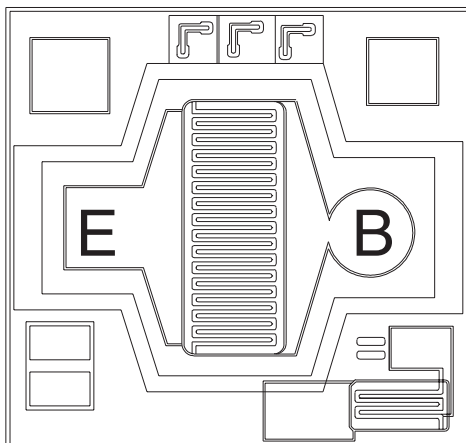
**PROCESS CP618**  
**Small Signal Transistor**  
PNP - Silicon RF Transistor Chip

**Central**<sup>TM</sup>  
**Semiconductor Corp.**

**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	21.7 x 21.7 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	3.5 MILS DIAMETER
Emitter Bonding Pad Area	3.5 x 3.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 10,000Å

**GEOMETRY**



R0

BACKSIDE COLLECTOR

**GROSS DIE PER 4 INCH WAFER**

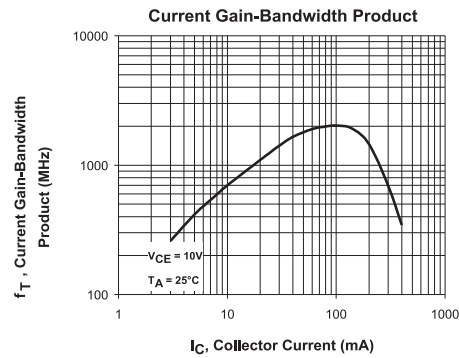
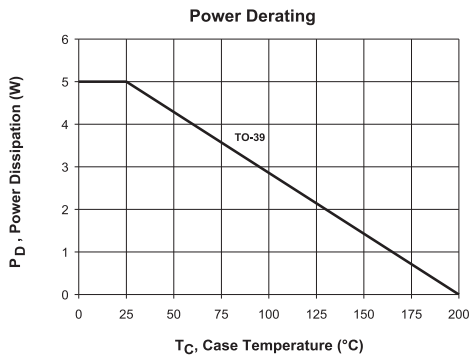
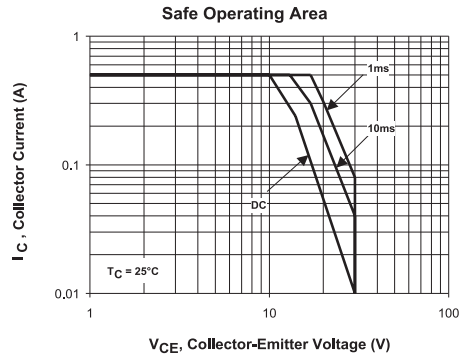
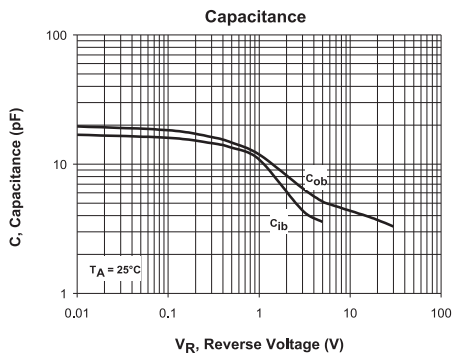
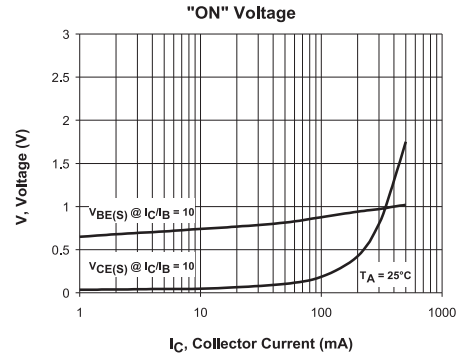
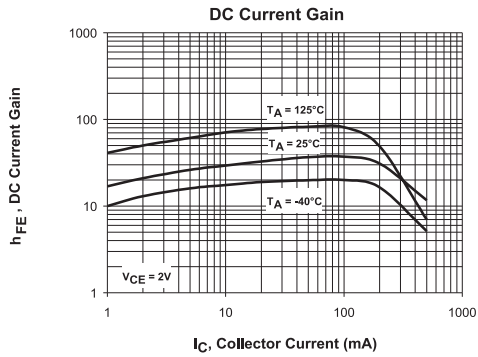
23,990

**PRINCIPAL DEVICE TYPES**

CM5583

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
www.centrasemi.com

R2 (1-August 2002)



145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
www.centalsemi.com

R2 (1-August 2002)